

GR-10E001DJ: E-mode GaN Power Transistor

Description

GR-10E001DJ is an enhancement mode GaN on Silicon power transistor. 10E001DJ provides high current and high operating speed which is suitable for DC to DC power supply applications.

Key Specifications

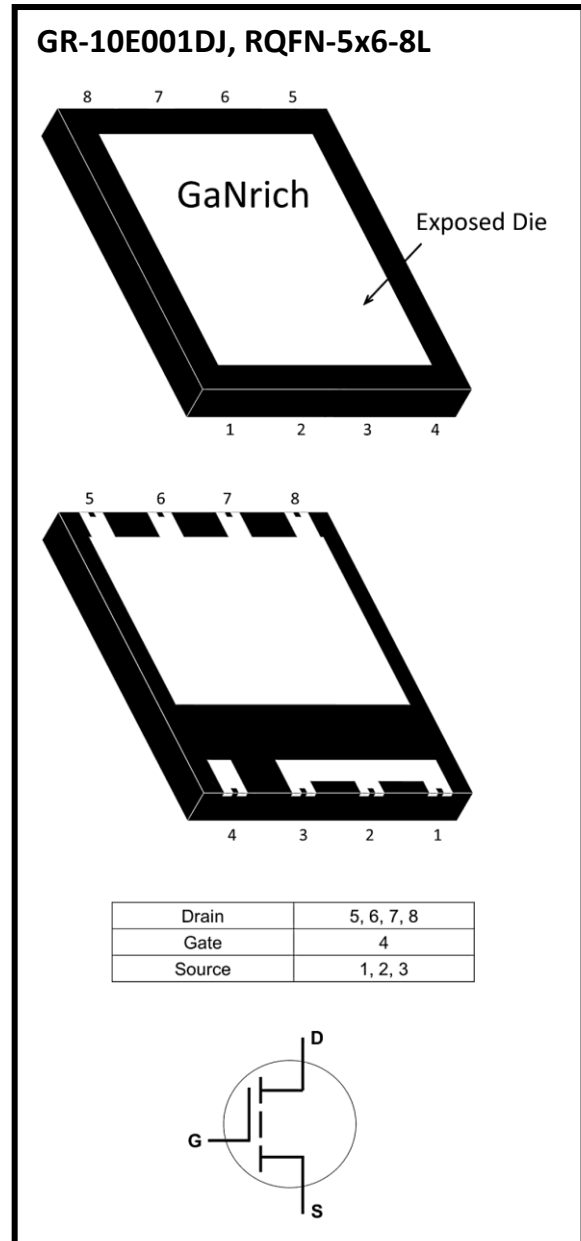
Part Number	GR-10E001DJ
V_{DS} , min.	100V
I_{DS} , Pulse (25°C, TPULSE = 10μs)	307A
$R_{DS(ON)}$, typ. @Vgs=6V	1.2mΩ
Q_G , typ.	28.5nC

Features

- 100 V enhancement mode power transistor
- High operating frequency
- $R_{DS(on)}$ = Typ. 1.2 mΩ
- RoHS compliant
- Zero QRR.

Applications

- High-Efficiency Synchronous Rectification (AC-DC/ DC-DC)
- High-Frequency Multi-Topology DC-DC Converters
- High-Power Density DC-DC Power Modules
- Industrial & Automotive Motor Drives



1. Electrical Characteristics

➤ **Table 1 Absolute maximum ratings**

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-source voltage	100	V
$V_{(TR)DSS}$	Transient drain to source voltage ^a	120	V
V_{GSS}	Gate- source voltage	-6V ~ +6V	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$ operation	99	A
	Drain current (continuous) at $T_C = 100^\circ\text{C}$ operation	68	A
$I_{D,Pulse}$	Pulsed drain current (pulse width: $10\mu\text{s}$, $V_{GS}=5\text{V}$) ^b	307	A
T_J	Operating temperature	-40 to +150	$^\circ\text{C}$
T_S	Storage temperature	-40 to +150	$^\circ\text{C}$
MSL	Moisture sensitivity level	MSL3	

a. In off-state, spike duty cycle $D < 0.01$, spike duration $< 1\mu\text{s}$

b. Defined by product design and characterization. Value is not tested to full current in production

➤ **Table 2 Thermal Characteristics**

Symbol	Parameter	Value	Unit
$R_{\theta JC_Top}$	Thermal resistance junction-case, Top	0.50	$^\circ\text{C}/\text{W}$
$R_{\theta JC_Bot}$	Thermal resistance junction-case, Bottom	0.50	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal resistance junction-ambient	60	$^\circ\text{C}/\text{W}$

a. Tested in package DFN-5x6.

➤ **Table 3** Electrical Characteristics ($T_{CASE} = 25\text{ }^{\circ}\text{C}$ unless otherwise stated)

Symbol	Parameter	Conditions	Values			Unit
			min.	typ.	max.	
V_{DSS}	Drain-source voltage	$V_{GS}=0V, I_D=200\mu A$	100	-	-	V
$V_{GS(th)}$	Gate threshold voltage	$V_G = V_D, I_D=1mA$	1.0	1.9	2.5	V
$R_{DS(on)}$	Drain-source on-resistance	$V_{GS}=6V, I_D=20A$	-	1.2	1.6	$m\Omega$
I_{DSS}	Drain-source leakage current	$V_{GS}=0V, V_{DS}=80V$	-	10	800	μA
I_{GSS}	Gate-to-Source Forward Leakage current	$V_{GS}=5V, V_{DS}=0V$	-	0.19	38.0	mA
	Gate-to-Source Forward Leakage current	$V_{GS}=5V, V_{DS}=0V, T_J=125^{\circ}\text{C}$	-	1.5	45.0	mA
	Gate-to-Source Reverse Leakage current	$V_{GS}=-4V, V_{DS}=0V$	-	0.15	4.5	mA
C_{ISS}	Input capacitance	$V_{GS}=0V, V_{DS}=50V$	-	3690	-	pF
C_{OSS}	Output capacitance		-	1765	-	
C_{RSS}	Reverse transfer capacitance		-	85	-	
Q_G	Gate charge	$V_{GS}=5V, V_{DS}=50V, I_D=20A$	-	28.5	-	nC
Q_{GS}	Gate-source charge	$V_{DS}=50V, I_D=20A$	-	5.4	-	
Q_{GD}	Gate-drain charge		-	3.2	-	
Q_{OSS}	Output charge	$V_{GS}=0V, V_{DS}=50V$	-	80	-	nC
Q_{RR}	Source-Drain Recovery Charge	-	-	0	-	nC

2. Typical Characteristic Curves

Fig 1. On-Region Characteristics

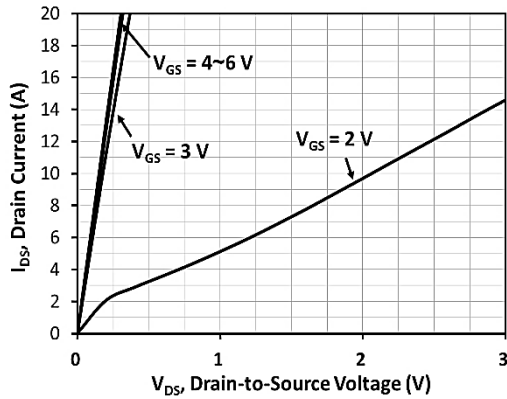


Fig 2. On-Resistance vs Drain Current and Temperature

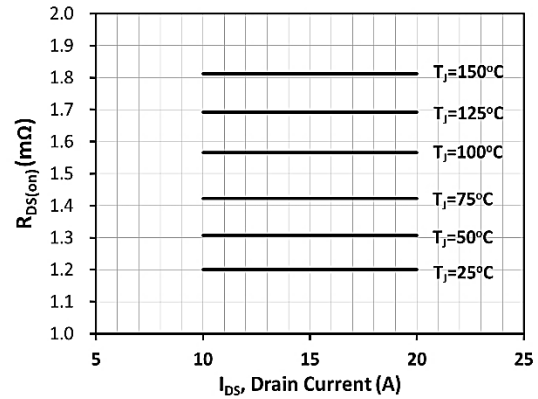


Fig 3. On-Resistance with Drain Current

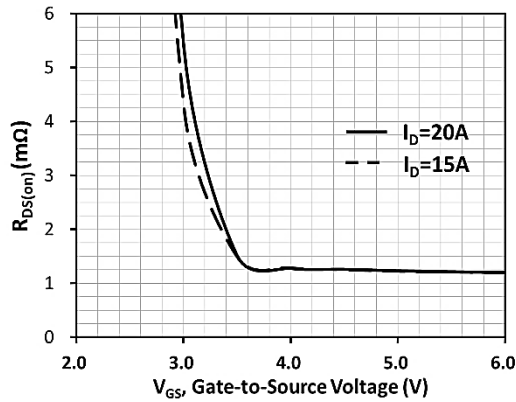


Fig 4. On-Resistance Variation with Temperature

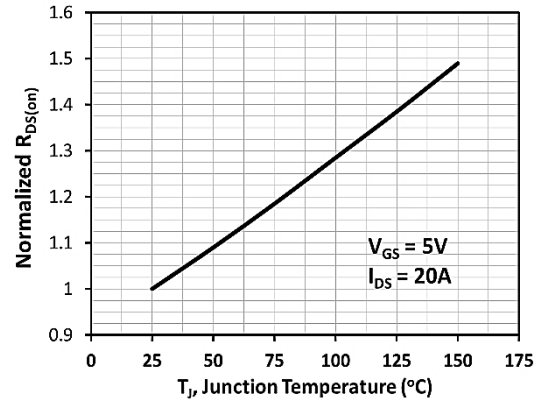


Fig 5. Threshold Voltage with Temperature

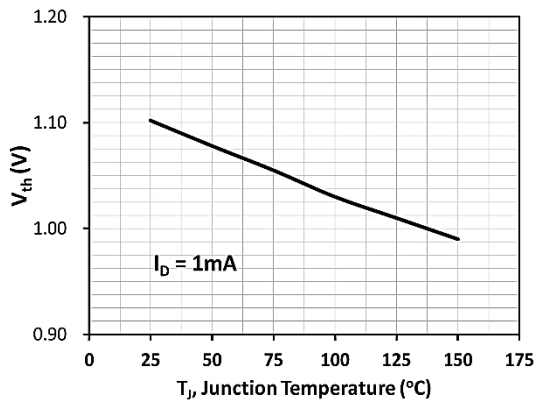


Fig 6. Capacitance Characteristics

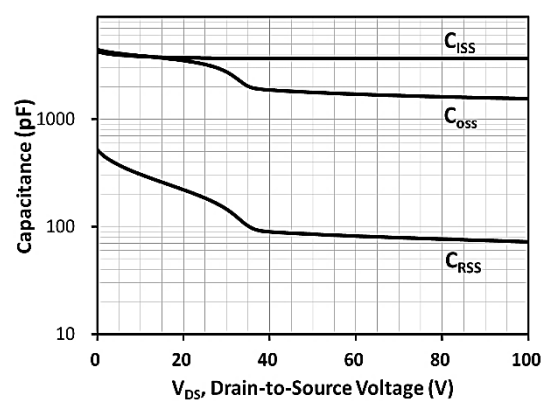


Fig 7. Gate Charge Characteristics, Qg

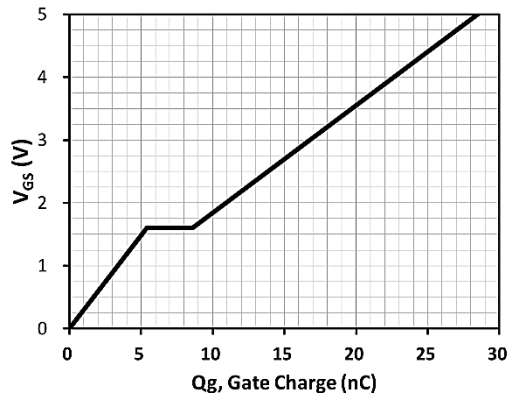


Fig 8. Capacitance Characteristics, Qoss

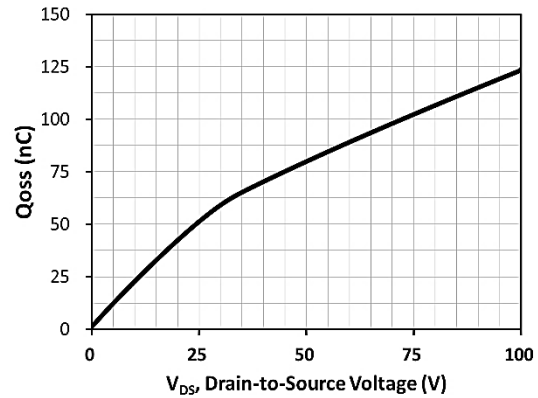
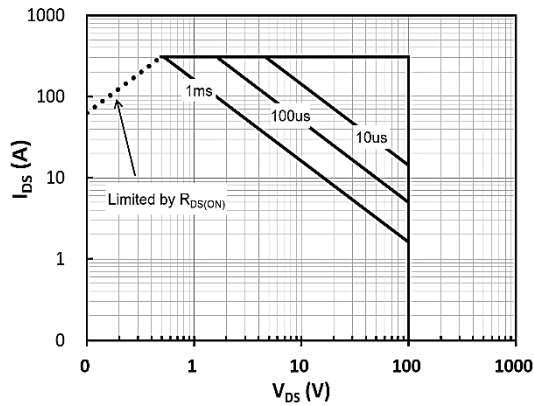
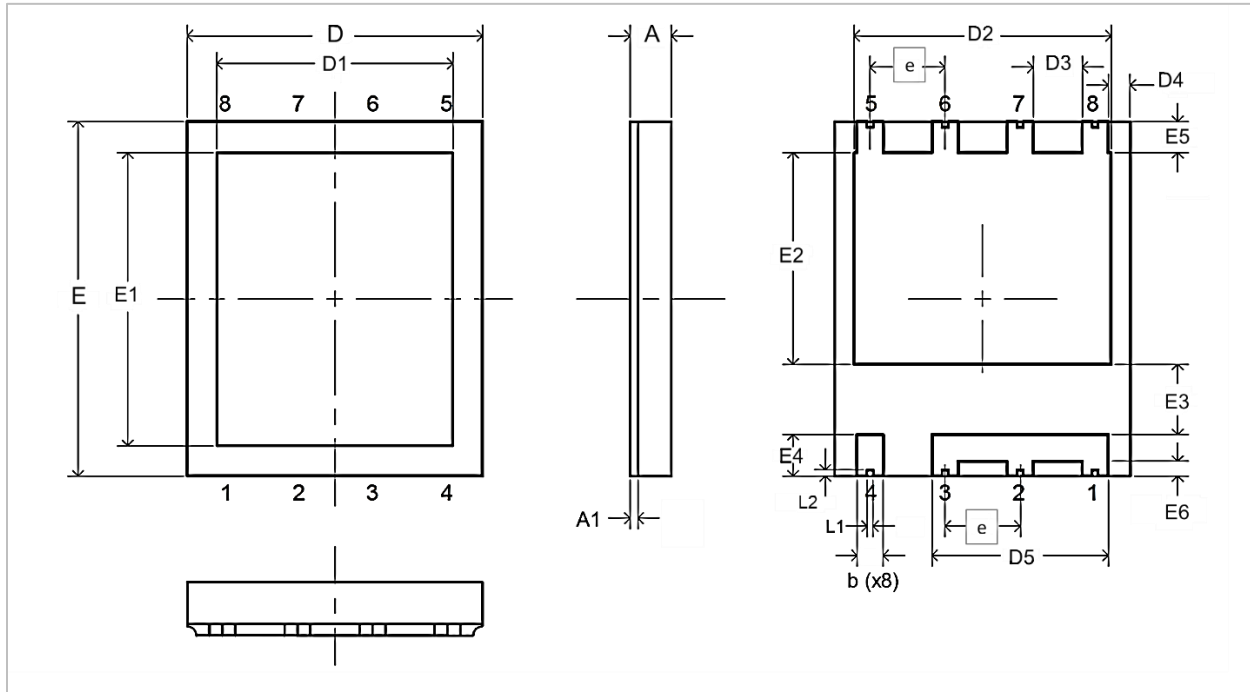


Fig 9. Safe Operating Area



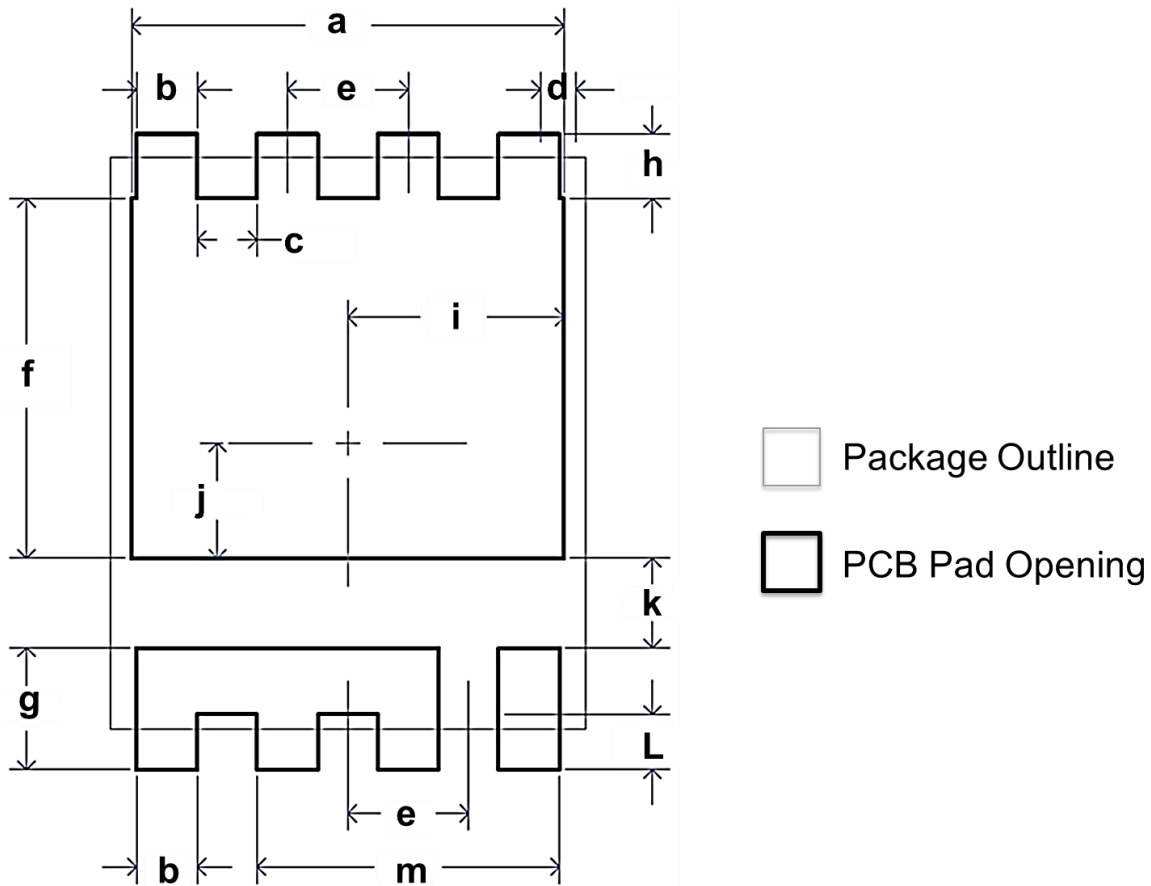
3. Package Outline Dimensions



➤ Table 4 Dimension of GR-RQFN-5x6-8L

SYMBOL	DIMENSION (IN MM)			SYMBOL	DIMENSION (IN MM)		
	MIN.	NOM.	MAX.		MIN.	NOM.	MAX.
A	---	---	0.70	D5	2.88	2.98	3.08
A1	0.13			E1	4.957 REF		
A2	0.42	0.45	0.48	E2	3.48	3.58	3.68
D	4.90	5.00	5.10	E3	1.09	1.19	1.29
E	2.90	6.00	3.10	E4	0.60	0.70	0.80
e	1.27 BSC			E5	0.43	0.53	0.63
b	0.34	0.44	0.54	E6	0.15	0.25	0.35
D1	3.994 REF			L1	0.05	0.10	0.20
D2	4.25	4.35	4.45	L2	0.05	0.10	0.20
D3	0.73	0.83	0.93				
D4	0.275	0.375	0.475				

4. Recommended PCB footprint



➤ Table 5 PCB Footprint Dimension

SYMBOL	DIMENSION	SYMBOL	DIMENSION
a	4.550	h	0.680
b	0.640	i	2.275
c	0.630	j	1.210
d	0.375	k	0.940
e	1.270	L	0.580
f	3.780	m	3.180
g	1.280	-	-

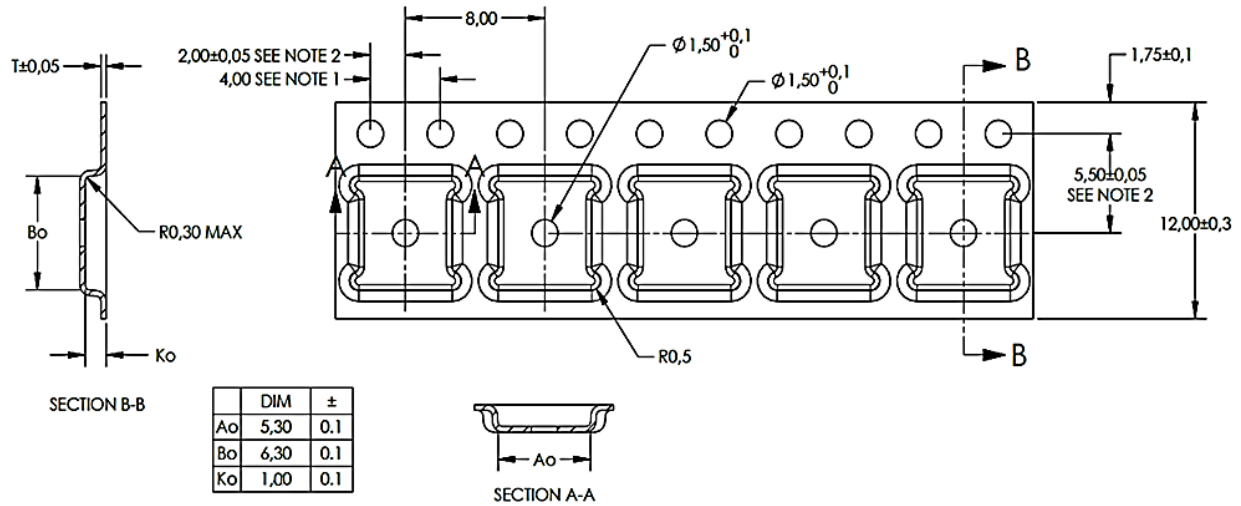
Notes:

(1) All dimensions are in mm.

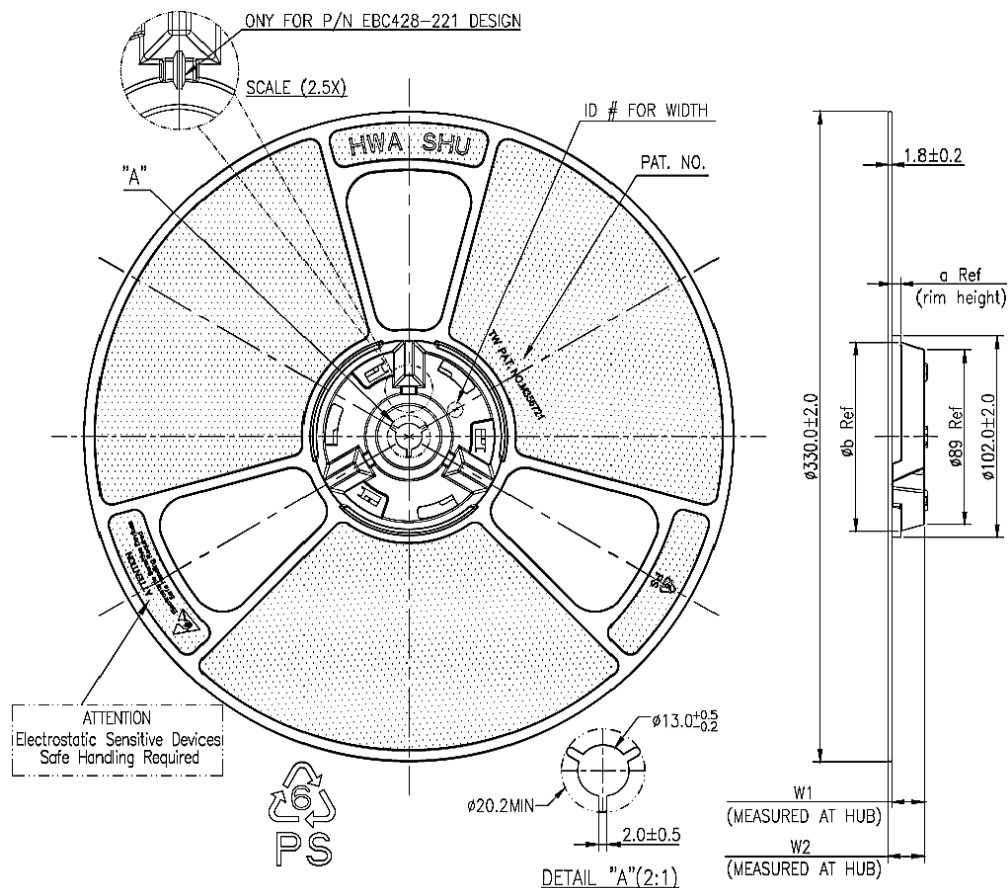
(2) Drawing is not to Scale.

5. Tape & Reel Information

13" Reel, Carrier Tape W=12mm



Unit: mm



6. Change Log

Version	Date	Description
0.1	March 28, 2025	Initial version
0.2	September 26, 2025	Revised version
0.3	April 16, 2026	Electrical characteristics revised

- **Note:** GaNrich semiconductor reserves the right to revise products and/or specifications without notice.